



Thyristor Module

$V_{RRM} = 2 \times 1200 \text{ V}$

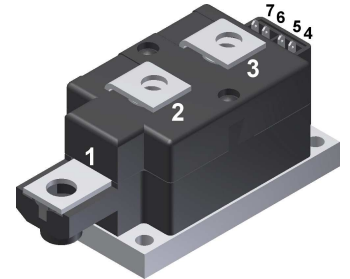
$I_{TAV} = 220 \text{ A}$

$V_T = 1.18 \text{ V}$

Phase leg

Part number

MCC225-12io1



Backside: isolated



Features / Advantages:

- International standard package
- Direct copper bonded Al₂O₃-ceramic with copper base plate
- Planar passivated chip
- Keyed gate/cathode twin pins

Applications:

- Motor control, softstarter
- Power converter
- Heat and temperature control for industrial furnaces and chemical processes
- Lighting control
- Solid state switches

Package: Y1

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: Copper internally DCB isolated
- Advanced power cycling

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| Rectifier | | | Ratings | | | |
|----------------|--|---|---------------------------|------|-------|-------------------|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
| $V_{RSM/DSM}$ | max. non-repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 1300 | V |
| $V_{RRM/DRM}$ | max. repetitive reverse/forward blocking voltage | $T_{VJ} = 25^{\circ}C$ | | | 1200 | V |
| I_{RD} | reverse current, drain current | $V_{R/D} = 1200 V$ | $T_{VJ} = 25^{\circ}C$ | | 1 | mA |
| | | $V_{R/D} = 1200 V$ | $T_{VJ} = 125^{\circ}C$ | | 40 | mA |
| V_T | forward voltage drop | $I_T = 200 A$ | $T_{VJ} = 25^{\circ}C$ | | 1.04 | V |
| | | $I_T = 400 A$ | | | 0.97 | V |
| | | $I_T = 200 A$ | $T_{VJ} = 125^{\circ}C$ | | 1.18 | V |
| | | $I_T = 400 A$ | | | 1.14 | V |
| I_{TAV} | average forward current | $T_C = 85^{\circ}C$ | $T_{VJ} = 140^{\circ}C$ | | 220 | A |
| $I_{T(RMS)}$ | RMS forward current | 180° sine | | | 400 | A |
| V_{T0} | threshold voltage | } for power loss calculation only | $T_{VJ} = 140^{\circ}C$ | | 0.79 | V |
| r_T | slope resistance | | | | 0.83 | mΩ |
| R_{thJC} | thermal resistance junction to case | | | | 0.157 | K/W |
| R_{thCH} | thermal resistance case to heatsink | | | 0.04 | | K/W |
| P_{tot} | total power dissipation | | $T_C = 25^{\circ}C$ | | 730 | W |
| I_{TSM} | max. forward surge current | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 45^{\circ}C$ | | 8.00 | kA |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 8.64 | kA |
| | | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 140^{\circ}C$ | | 6.80 | kA |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 7.35 | kA |
| I^2t | value for fusing | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 45^{\circ}C$ | | 320.0 | kA ² s |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 310.5 | kA ² s |
| | | $t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$ | $T_{VJ} = 140^{\circ}C$ | | 231.2 | kA ² s |
| | | $t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$ | $V_R = 0 V$ | | 224.4 | kA ² s |
| C_J | junction capacitance | $V_R = 400 V \quad f = 1 \text{ MHz}$ | $T_{VJ} = 25^{\circ}C$ | | 366 | pF |
| P_{GM} | max. gate power dissipation | $t_p = 30 \mu s$ | $T_C = 140^{\circ}C$ | | 120 | W |
| | | $t_p = 500 \mu s$ | | | 60 | W |
| P_{GAV} | average gate power dissipation | | | | 20 | W |
| $(di/dt)_{cr}$ | critical rate of rise of current | $T_{VJ} = 140^{\circ}C; f = 50 \text{ Hz}$ | repetitive, $I_T = 660 A$ | | 100 | A/μs |
| | | $t_p = 200 \mu s; di_G/dt = 1 A/\mu s;$ | non-repet., $I_T = 220 A$ | | 500 | A/μs |
| $(dv/dt)_{cr}$ | critical rate of rise of voltage | $V = \frac{2}{3} V_{DRM}$ | $T_{VJ} = 140^{\circ}C$ | | 1000 | V/μs |
| | | $R_{GK} = \infty; \text{method 1 (linear voltage rise)}$ | | | | |
| V_{GT} | gate trigger voltage | $V_D = 6 V$ | $T_{VJ} = 25^{\circ}C$ | | 2 | V |
| | | | $T_{VJ} = -40^{\circ}C$ | | 3 | V |
| I_{GT} | gate trigger current | $V_D = 6 V$ | $T_{VJ} = 25^{\circ}C$ | | 150 | mA |
| | | | $T_{VJ} = -40^{\circ}C$ | | 220 | mA |
| V_{GD} | gate non-trigger voltage | $V_D = \frac{2}{3} V_{DRM}$ | $T_{VJ} = 140^{\circ}C$ | | 0.25 | V |
| I_{GD} | gate non-trigger current | | | | 10 | mA |
| I_L | latching current | $t_p = 30 \mu s$ | $T_{VJ} = 25^{\circ}C$ | | 200 | mA |
| | | $I_G = 0.45 A; di_G/dt = 0.45 A/\mu s$ | | | | |
| I_H | holding current | $V_D = 6 V \quad R_{GK} = \infty$ | $T_{VJ} = 25^{\circ}C$ | | 150 | mA |
| t_{gd} | gate controlled delay time | $V_D = \frac{1}{2} V_{DRM}$ | $T_{VJ} = 25^{\circ}C$ | | 2 | μs |
| | | $I_G = 1 A; di_G/dt = 1 A/\mu s$ | | | | |
| t_q | turn-off time | $V_R = 100 V; I_T = 220 A; V = \frac{2}{3} V_{DRM}$ | $T_{VJ} = 125^{\circ}C$ | | 200 | μs |
| | | $di/dt = 10 A/\mu s \quad dv/dt = 50 V/\mu s \quad t_p = 200 \mu s$ | | | | |



| Package Y1 | | | Ratings | | | |
|---------------|--|----------------------|---------|------|------|------|
| Symbol | Definition | Conditions | min. | typ. | max. | Unit |
| I_{RMS} | RMS current | per terminal | | | 600 | A |
| T_{VJ} | virtual junction temperature | | -40 | | 140 | °C |
| T_{op} | operation temperature | | -40 | | 125 | °C |
| T_{stg} | storage temperature | | -40 | | 125 | °C |
| Weight | | | | 680 | | g |
| M_D | mounting torque | | 4.5 | | 7 | Nm |
| M_T | terminal torque | | 11 | | 13 | Nm |
| $d_{Spp/App}$ | creepage distance on surface striking distance through air | terminal to terminal | 16.0 | | | mm |
| $d_{Spb/Apb}$ | | terminal to backside | 16.0 | | | mm |
| V_{ISOL} | isolation voltage | t = 1 second | 3600 | | | V |
| | | t = 1 minute | 3000 | | | V |



Data Matrix: part no. (1-19), DC + PI (20-25), lot.no.# (26-31), blank (32), serial no.# (33-36)

| Ordering | Ordering Number | Marking on Product | Delivery Mode | Quantity | Code No. |
|----------|-----------------|--------------------|---------------|----------|----------|
| Standard | MCC225-12io1 | MCC225-12io1 | Box | 3 | 463280 |

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 140^{\circ}C$

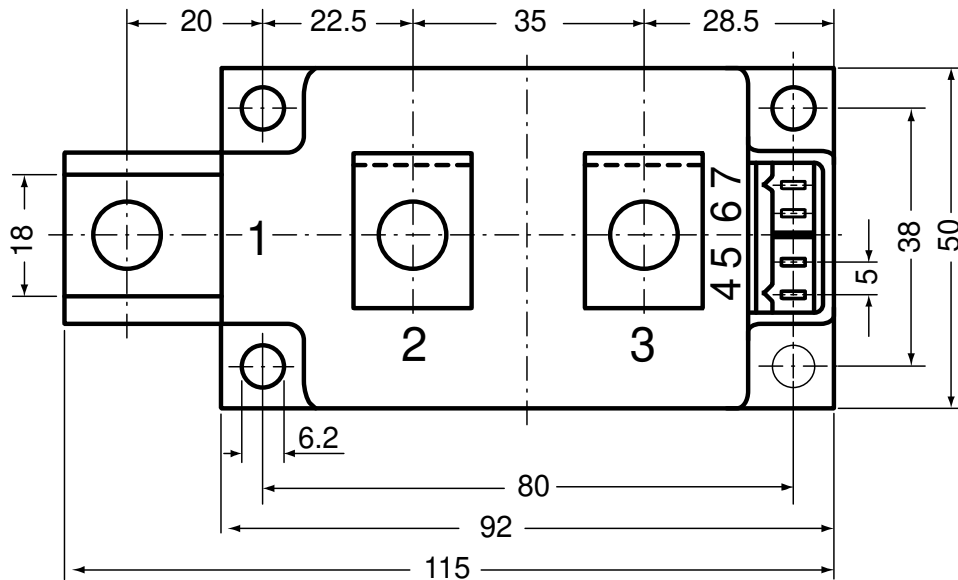
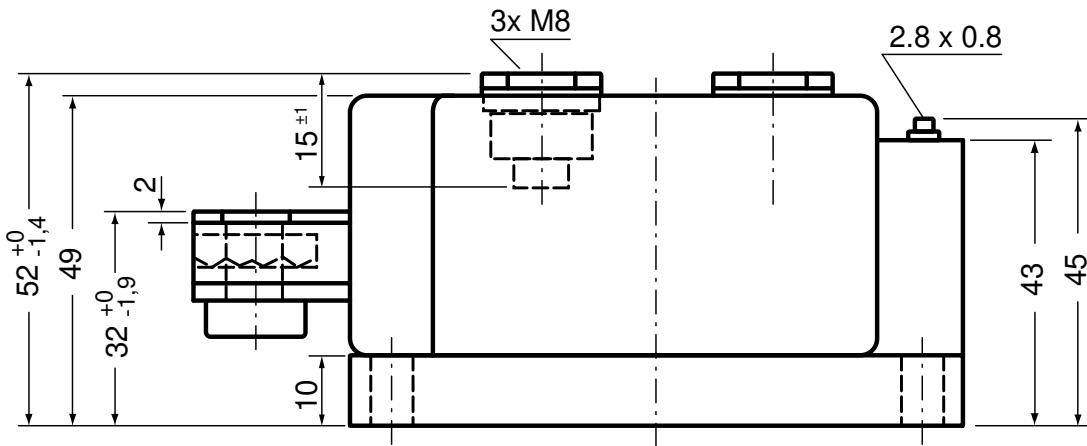


Thyristor

| | | | |
|--------------|--------------------|------|----|
| $V_{0\ max}$ | threshold voltage | 0.79 | V |
| $R_{0\ max}$ | slope resistance * | 0.64 | mΩ |



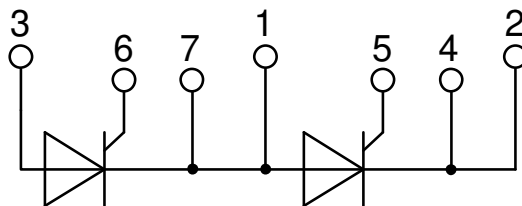
Outlines Y1



Optional accessories for modules

Keyed gate/cathode twin plugs with wire length = 350 mm, gate = white, cathode = red

Type ZY 180L (L = Left for pin pair 4/5)
Type ZY 180R (R = Right for pin pair 6/7) } UL 758, style 3751



Thyristor

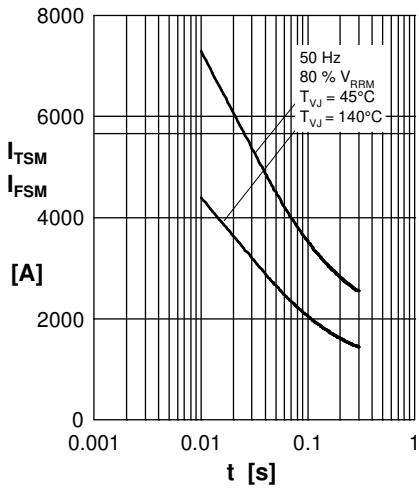


Fig. 1 Surge overload current
 $I_{TSM/FSM}$: Crest value, t : duration



Fig. 2 I^2dt versus time



Fig. 3 Max. forward current at case temperature

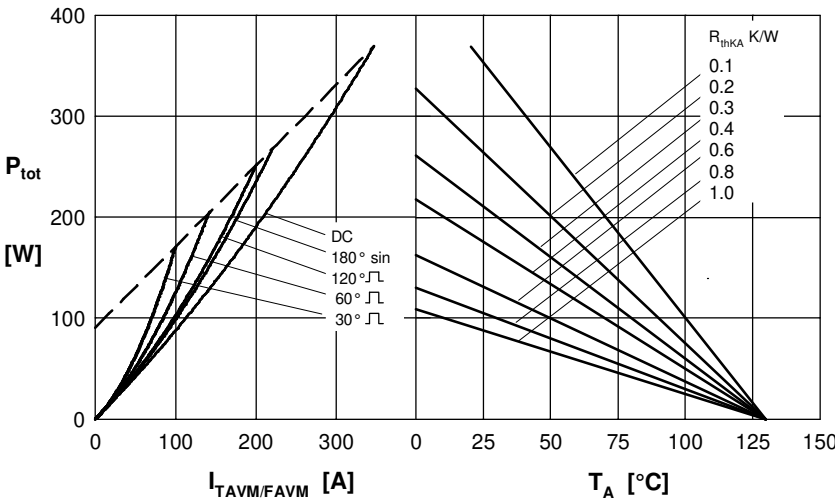


Fig. 4 Power dissipation versus on-state current and ambient temperature (per thyristor or diode)

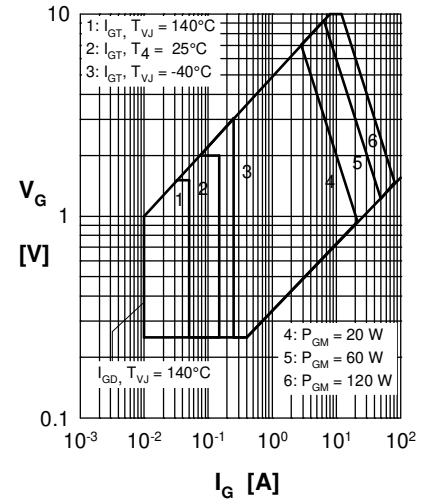


Fig. 5 Gate voltage and current

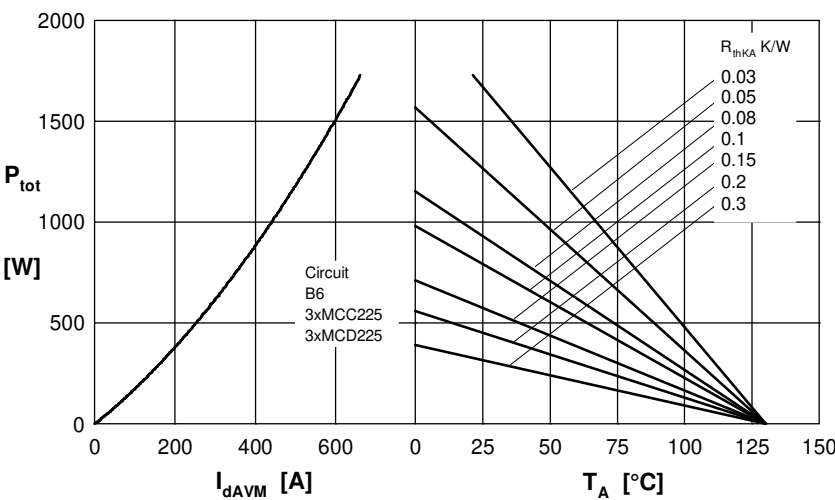


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature



Fig. 7 Gate trigger characteristics

Rectifier

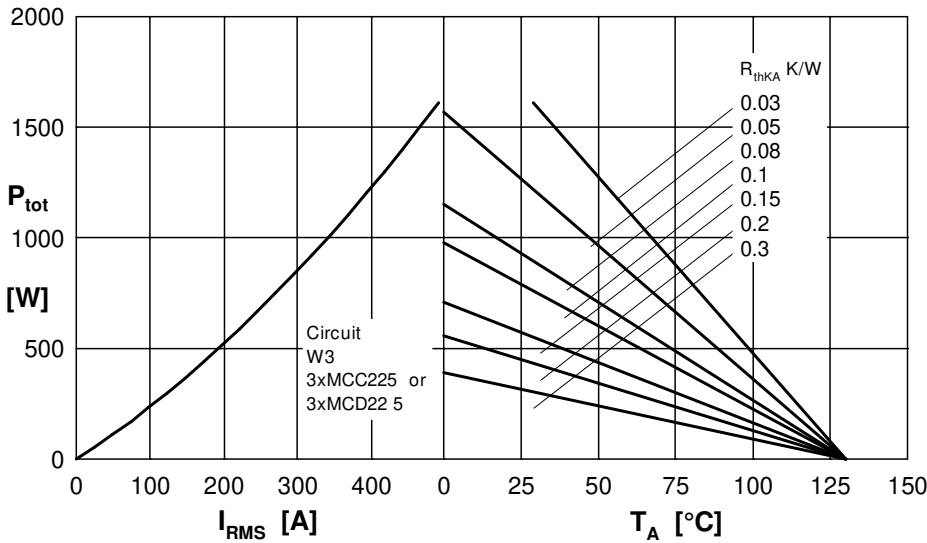


Fig. 8 Three phase AC-controller: Power dissipation versus R_{MS} output current and ambient temperature



Fig. 9 Forward characteristics

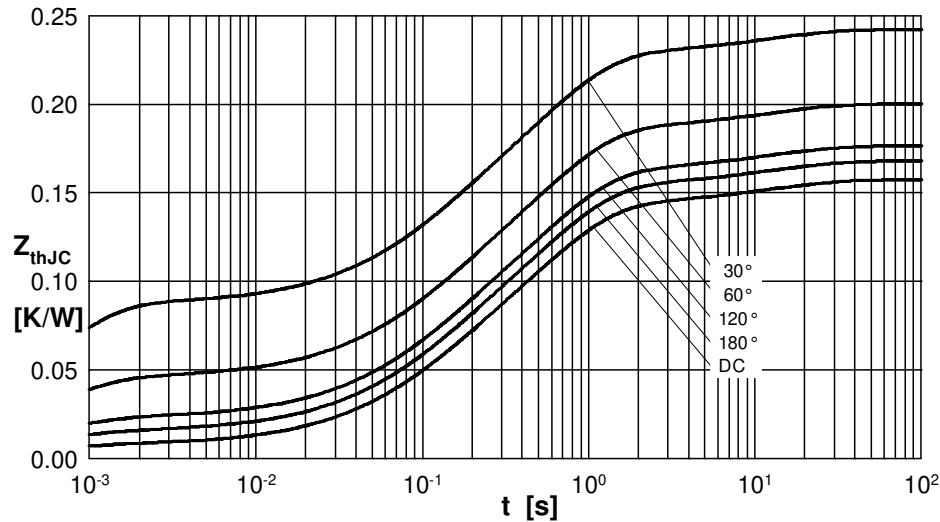


Fig. 10 Transient thermal impedance junction to case (per thyristor/diode)

R_{thJC} for various conduct. angles d:

| d | R_{thJC} (K/W) |
|------|------------------|
| DC | 0.157 |
| 180° | 0.168 |
| 120° | 0.177 |
| 60° | 0.200 |
| 30° | 0.243 |

Constants for Z_{thJC} calculation:

| i | R_{thi} (K/W) | t (s) |
|---|-----------------|---------|
| 1 | 0.0076 | 0.00054 |
| 2 | 0.0406 | 0.09800 |
| 3 | 0.0944 | 0.54000 |
| 4 | 0.0147 | 12.0000 |



Fig. 11 Transient thermal impedance junction to heatsink (per thyristor/diode)

R_{thJK} for various conduct. angles d:

| d | R_{thJK} (K/W) |
|------|------------------|
| DC | 0.197 |
| 180° | 0.208 |
| 120° | 0.217 |
| 60° | 0.240 |
| 30° | 0.283 |

Constants for Z_{thJK} calculation:

| i | R_{thi} (K/W) | t (s) |
|---|-----------------|---------|
| 1 | 0.0076 | 0.00054 |
| 2 | 0.0406 | 0.09800 |
| 3 | 0.0944 | 0.54000 |
| 4 | 0.0147 | 12.0000 |
| 5 | 0.0400 | 12.0000 |

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